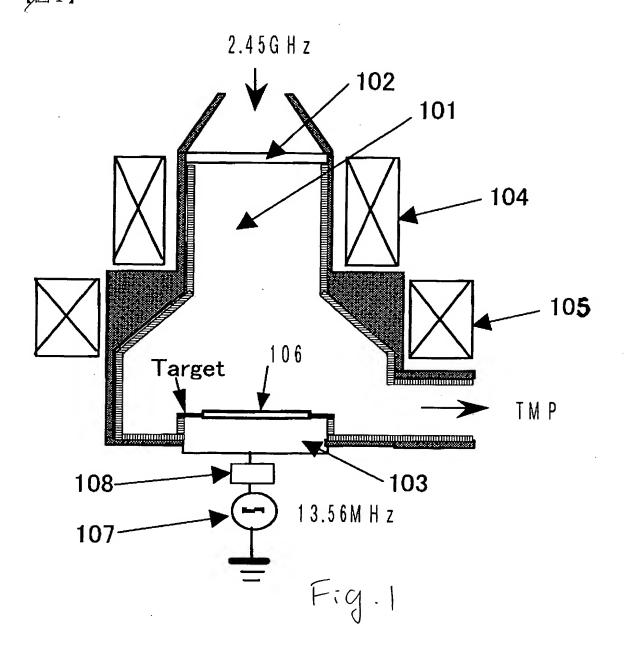


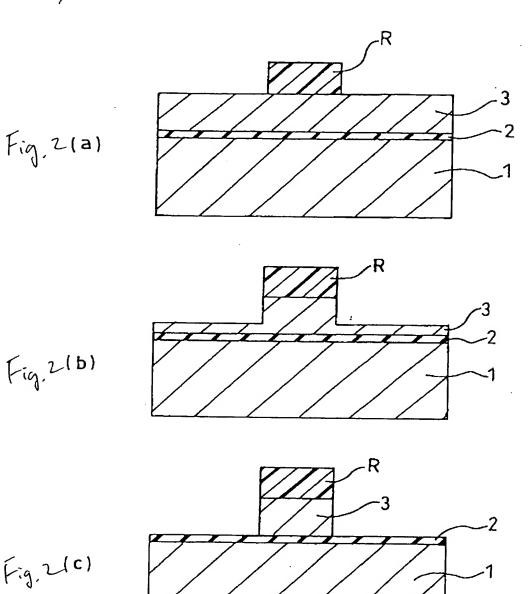
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Fig. 2(b)

Fig. 210)



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Phone No.: (612) 371-5237

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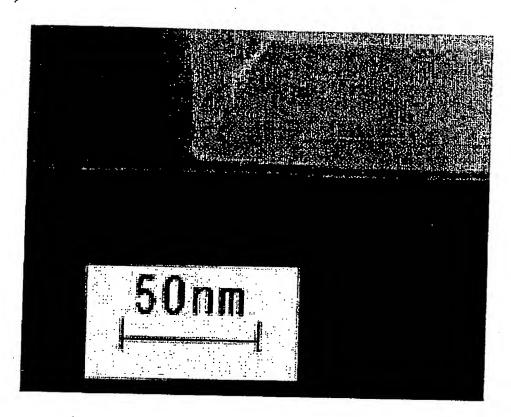


Fig. 3

【図4】

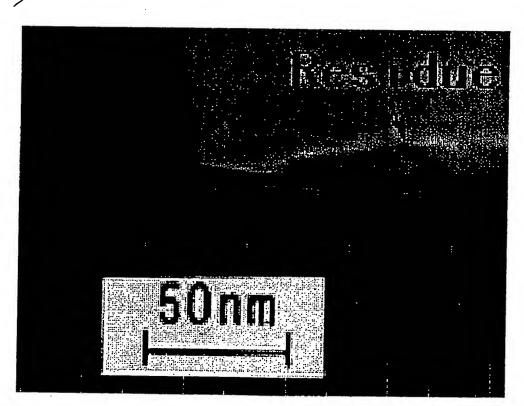


Fig.4

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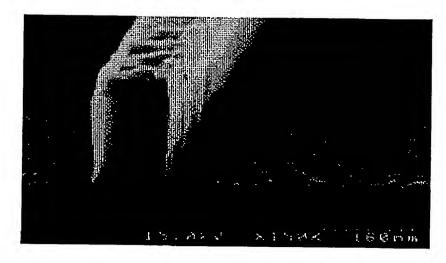


Fig.5

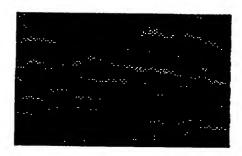


Fig 6 (a) partially etched polySi

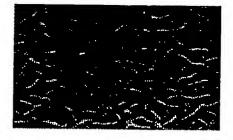
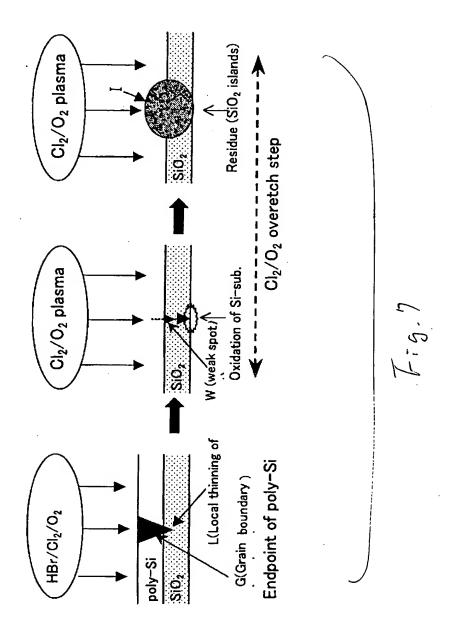


Fig. 6 (b)gate oxide surface Surface morphology of polySi and gate oxide.

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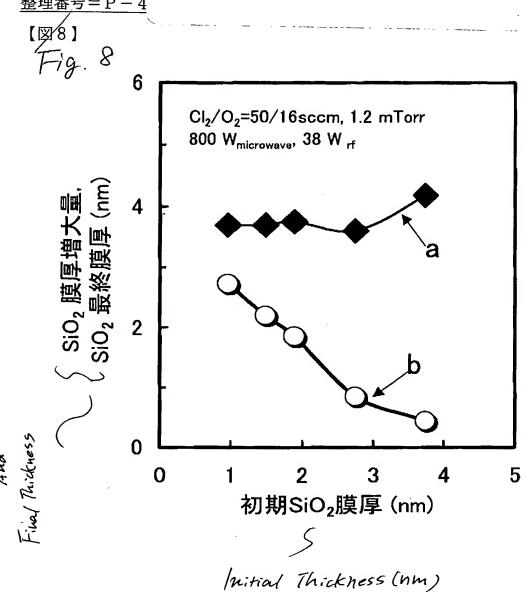
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Increase of Thickness

Inventor: Tabara

Docket No.: 12844.0045US01 Title: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE Attorney Name: Douglas P. Mueller

Phone No.: (612) 371-5237

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